## PATENT ABSTRACTS OF JAPAN

(11)Publication number:

05-102189

(43)Date of publication of application: 23.04.1993

(51)Int.CI.

H01L 21/336

H01L 29/784

C23C 14/26 C30B 25/14

H01L 21/205

(21)Application number: 04-023986

(71)Applicant: FUJITSU LTD

(22)Date of filing:

10.02.1992

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(30)Priority

Priority number: 03202088

Priority date: 13.08.1991

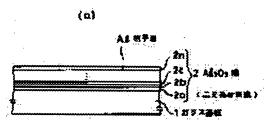
Priority country: JP

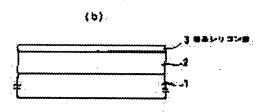
## (54) FORMATION METHOD OF THIN FILM, SILICON THIN FILM AND FORMATION METHOD OF SILICON THIN-FILM TRANSISTOR

## (57)Abstract:

PURPOSE: To obtain a silicon thin film whose crystallinity at a low temperature is good by a method wherein a binary material film is grown on a substrate and, in succession, the silicon film is grown on the binary material film by an atomic-layer deposition method wherein the substrate is exposed alternately to two atmospheres which separately contain individual atoms constituting a binary material.

CONSTITUTION: By using an atomic-layer deposition method wherein a substrate 1 is exposed alternately to two atmospheres which contain individual atoms constituting a binary material, a binary material film 2 is grown on the substrate 1, and, in succession, a silicon film 3 is grown on the binary material film 2. Thereby, it is possible to obtain the silicon film whose crystallinity is good.





## **LEGAL STATUS**

[Date of request for examination]

10.02.1992

[Date of sending the examiner's decision of rejection] 17.10.1995

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

2828152

[Date of registration] 18.09,1998